





### **N-CHANNEL ENHANCEMENT MODE MOSFET**

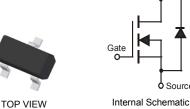
### **Features**

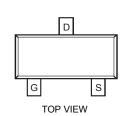
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)







## Ordering Information (Note 4)

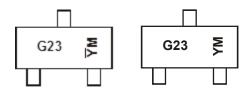
Part Number	Case	Packaging		
DMG2302U-7	SOT-23	3000/Tape & Reel		

Drain

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

## **Marking Information**



G23 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) \(\bar{Y}\)M = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{Y}$  = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Υ		7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** @TA = +25°C unless otherwise specified

Characte	ristic		Symbol	Value	Units
Drain-Source Voltage		$V_{DSS}$	20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Continuous Drain Current (Note 5) Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	4.2 3.4	Α
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	27	Α

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	P	0.8 0.5	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°	$R_{\theta JA}$	156	°C/W	
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

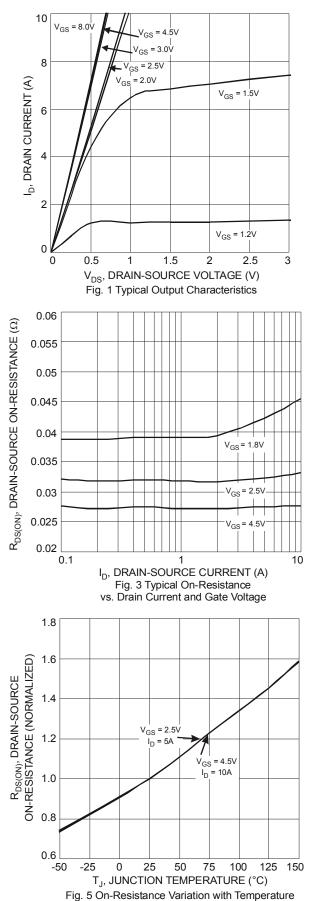
# **Electrical Characteristics** @T<sub>A</sub> = +25°C unless otherwise specified

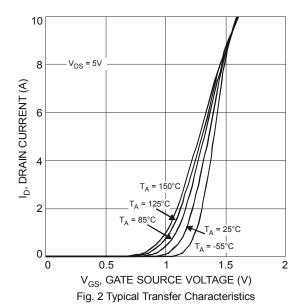
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)									
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$			
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$			
Gate-Source Leakage	I <sub>GSS</sub>	-	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	-	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 50\mu A$			
Static Drain-Source On-Resistance	D- 0 (0) 11			90 120	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$			
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_				$V_{GS} = 2.5V, I_D = 3.1A$			
Forward Transfer Admittance	Y <sub>fs</sub>	_	13	_	S	$V_{DS} = 5V, I_{D} = 3.6A$			
Diode Forward Voltage	$V_{SD}$	-	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	C <sub>iss</sub>	_	594.3	_	pF	101/1/			
Output Capacitance	Coss	1	64.5	_	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz			
Reverse Transfer Capacitance	C <sub>rss</sub>	_	57.7	_	pF	1 - 1.0WHZ			
Gate Resistance	$R_{g}$	-	1.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$			
Total Gate Charge	Qg	_	7.0	_	nC	45)/ )/ 40)/			
Gate-Source Charge	Qgs	-	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 3.6A$			
Gate-Drain Charge	$Q_{gd}$	-	1.4	_	nC	ID - 3.0A			
Turn-On Delay Time	t <sub>D(on)</sub>	-	7.4	_	ns				
Turn-On Rise Time	t <sub>r</sub>	-	9.8	_	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V,			
Turn-Off Delay Time	t <sub>D(off)</sub>	_	28.1	_	ns	$R_L = 2.78\Omega, R_G = 1.0\Omega$			
Turn-Off Fall Time	t <sub>f</sub>	_	6.7	_	ns				

Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.







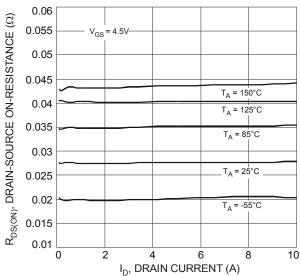
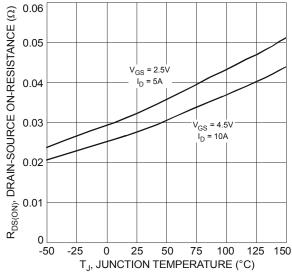
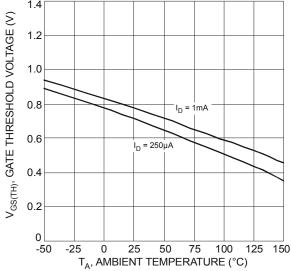


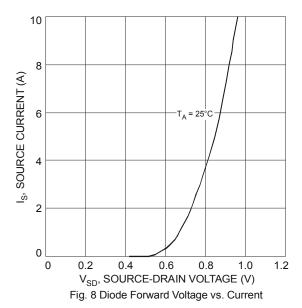
Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

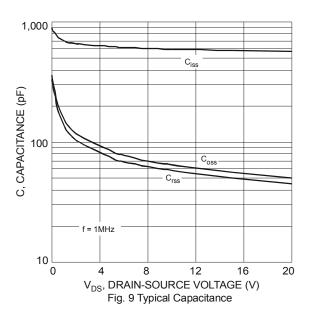


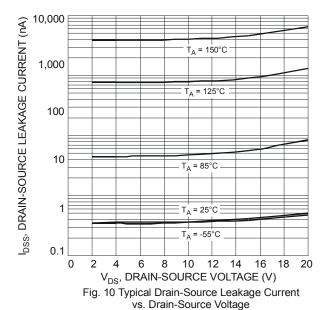












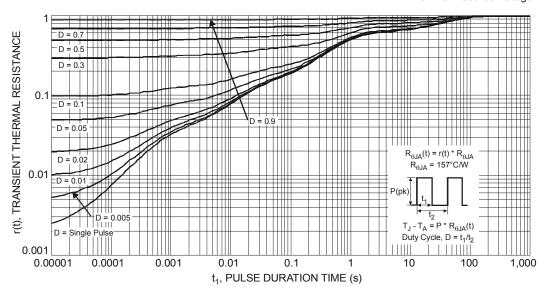
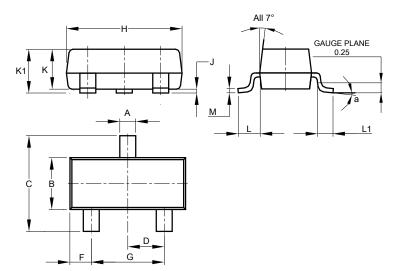


Fig. 11 Transient Thermal Response



## **Package Outline Dimensions**

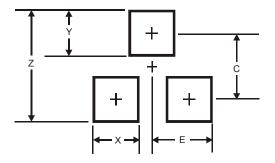
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
<b>K</b> 1	0.903	1.10	1.025				
٦	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	8°						
All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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